

U.S. Patent Application Serial No. 10/699,832
Amendment filed May 3, 2005
Reply to OA dated February 7, 2005

AMENDMENTS TO THE CLAIMS:

Please cancel claims 2 and 6-9 without prejudice or disclaimer. Please amend claims 1, 3 and 4 and add new claims 12 and 13 as follows. This listing of claims will replace all prior versions, and listings, of claims in the application:

Listing of Claims:

Claim 1 (Currently amended): A monocrystalline gallium nitride localized substrate, comprising:

~~an area of grown monocrystalline gallium nitride locally on~~ a monocrystalline silicon substrate;

a region of silicon carbide formed on the monocrystalline silicon substrate; and

a region of monocrystalline gallium nitride grown on the region of silicon carbide.

Claim 2 (Canceled).

Claim 3 (Currently amended): A monocrystalline gallium nitride localized substrate according to Claim 1, further comprising:

~~wherein said monocrystalline gallium nitride is grown by using~~ a region of silicon nitride as a mask formed on the monocrystalline silicon substrate along side of the region of silicon carbide.

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Claim 4 (Currently amended): A monocrystalline gallium nitride localized substrate according to Claim 1, further comprising:

~~wherein said monocrystalline gallium nitride is grown by using a region of silicon oxide as a mask~~ formed on the monocrystalline silicon substrate along side of the region of silicon carbide.

Claim 5 (Previously presented): A monocrystalline gallium nitride localized substrate according to Claim 1, wherein said monocrystalline silicon substrate is an SOI substrate.

Claims 6-9 (Canceled).

Claim 10 (Previously presented): A monocrystalline gallium nitride localized substrate according to Claim 3, wherein said monocrystalline silicon substrate is an SOI substrate.

Claim 11 (Previously presented): A monocrystalline gallium nitride localized substrate according to Claim 4, wherein said monocrystalline silicon substrate is an SOI substrate.

Claim 12 (New): A monocrystalline gallium nitride localized substrate according to claim 3, further comprising:

a region of polycrystalline gallium nitride grown on the region of silicon nitride.

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Claim 13 (New): A monocrystalline gallium nitride localized substrate according to claim 4, further comprising:

a region of polycrystalline gallium nitride grown on the region of silicon oxide.